

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-15. (canceled).

16. (new) A semiconductor interconnect structure comprising:

a substrate;

a first insulating film directly on said substrate;

a first interconnect through said first insulating film and directly contacting said substrate, said first interconnect comprising a trench having a metal barrier layer on walls and a bottom of said trench and a copper layer within said trench;

a first diffusion barrier film directly on said first insulating film;

a second diffusion barrier film directly on said first diffusion barrier film;

a second insulating film directly on said second diffusion barrier film; and

a second interconnect through said first and second diffusion barrier films and said second insulating film, said second interconnect comprising a trench having a metal barrier

layer on walls and a bottom of said trench and a copper layer within said trench.

17. (new) The interconnect structure as claimed in claim 16, wherein said first and second interconnects are axially aligned.

18. (new) The interconnect structure as claimed in claim 16, wherein said first diffusion barrier film and said bottom of said first interconnect are coplanar.

19. (new) The interconnect structure as claimed in claim 16, wherein said bottom of said second interconnect contacts said walls of said first interconnect.